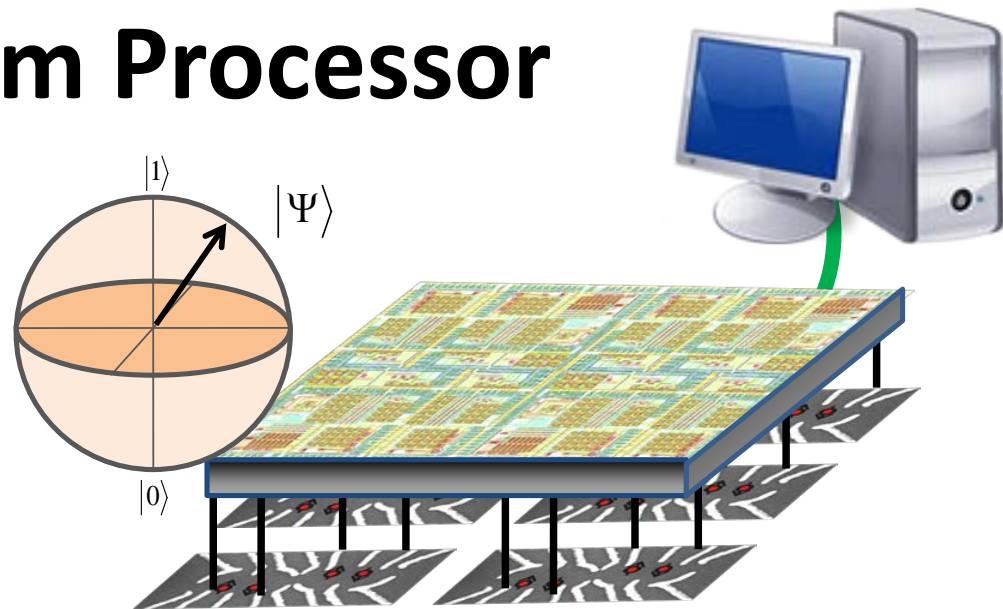
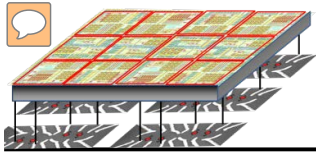




Design Considerations for Integrated Semiconductor Control Electronics for a Large-scale Solid State Quantum Processor

Hendrik Bluhm
Andre Kruth
Lotte Geck
Carsten Degenhardt





Quantum Computing

Classical bits

0 or 1

N bits $\Rightarrow 2^N$ states 0, 1, ..., 2^N-1



Quantum bits

$\alpha|0\rangle + \beta|1\rangle$

N qubits: 2^N dimensional
Hilbert space

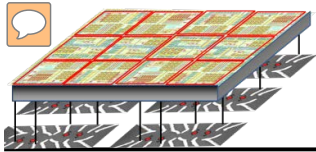
$|0\rangle, |1\rangle, \dots, |2^N-1\rangle$

Principles of quantum mechanics

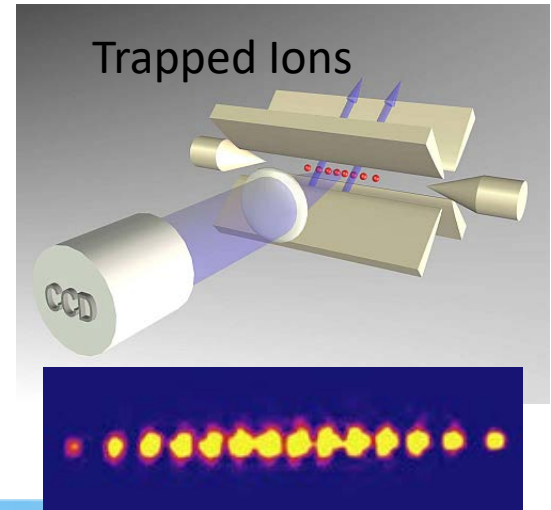
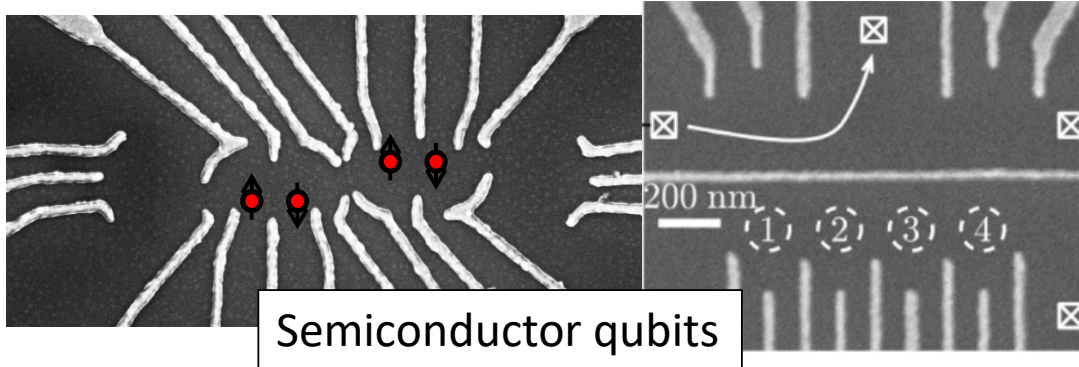
\Rightarrow Huge memory space

\Rightarrow Built-in parallelism

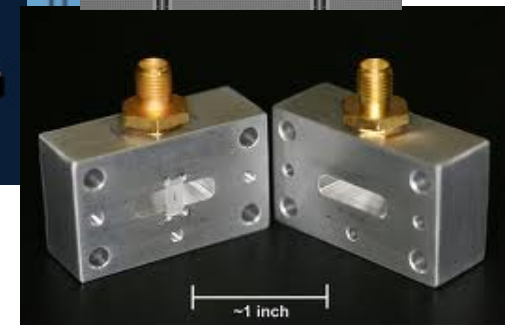
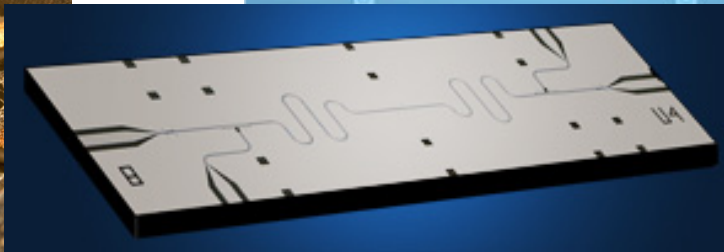
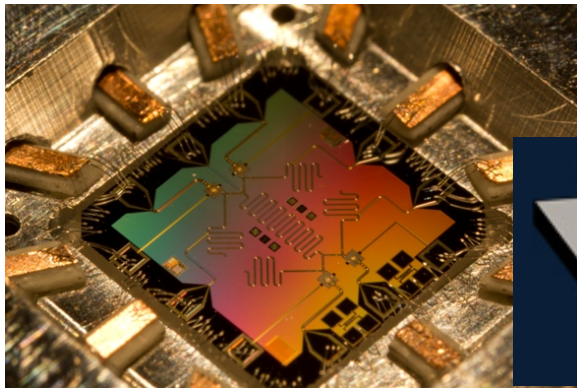
\Rightarrow Exponential speedup (for some problems)

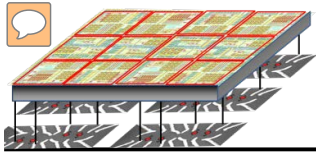


Qubit Zoo



Superconducting Qubits





Scaling Need for Applications

Prime factorization and decryption

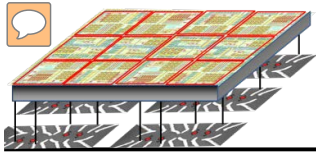
Predicted resource requirement

5×10^8 qubits, 1 day
for 1024 bit number

Quantum Chemistry

10^8 qubits, 13 days for $C_3H_7NO_2$
 10^6 qubits for Fe_2S_2

- Catalyst design for CO_2 capture or fertilizer production
- Quantum material design



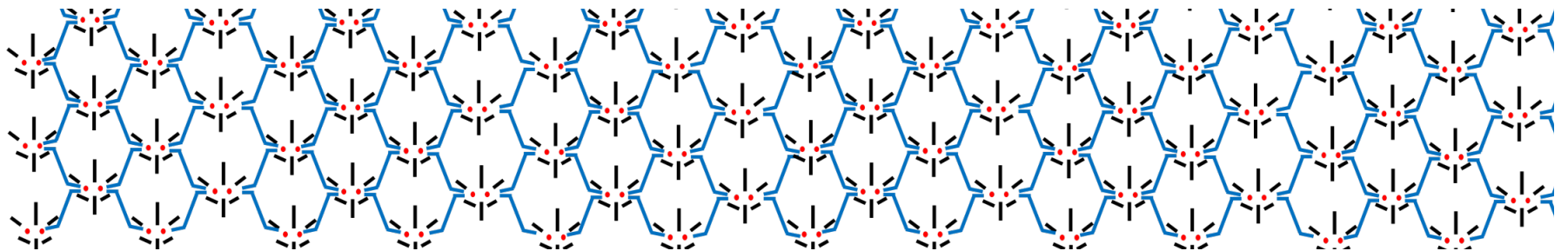
Quantum Computing Architecture

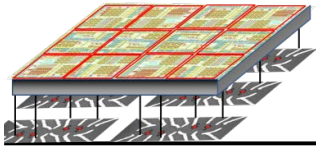
Requirements for surface-code error correction

- Lattice 2D nearest neighbor interaction
- Error rate $< 10^{-3}$

Resource needs for high impact computations

- ∩ 10000 logical, error corrected qubits
- ∩ x 1000 physical qubits per logical qubit
- ∩ x 10 overhead to work around drawbacks of error correction
- ∩ = 10^8 qubits



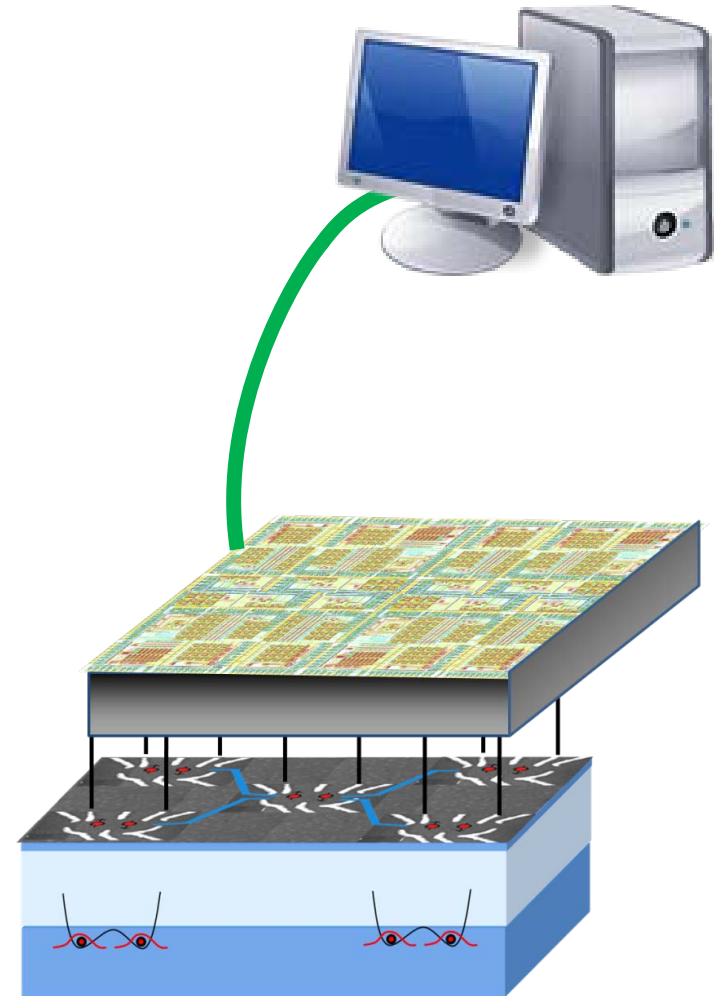


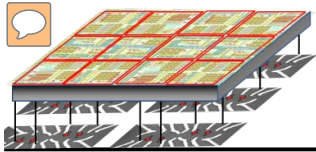
Outline

Requirements for scalable quantum computing

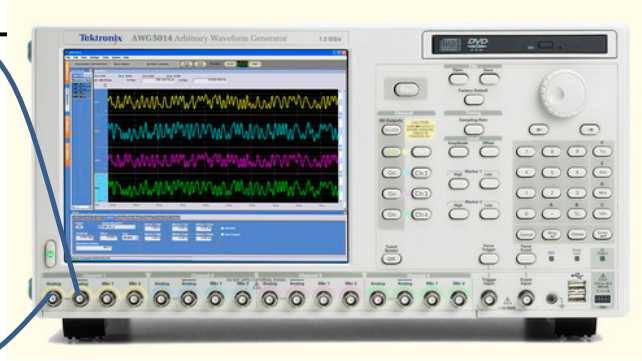
Vision of a scalable quantum processor

Ultra-low power control electronics





Brute Force Approach



) x N

Room temperature pulse generator

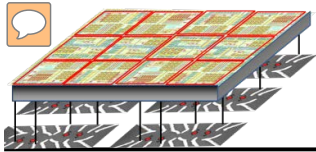
Scaling limitations

Control electronics

Thousands of racks

Wiring

1 coax cable per qubit
=> 1 m² scale wiring cross section
for 10⁶ qubits



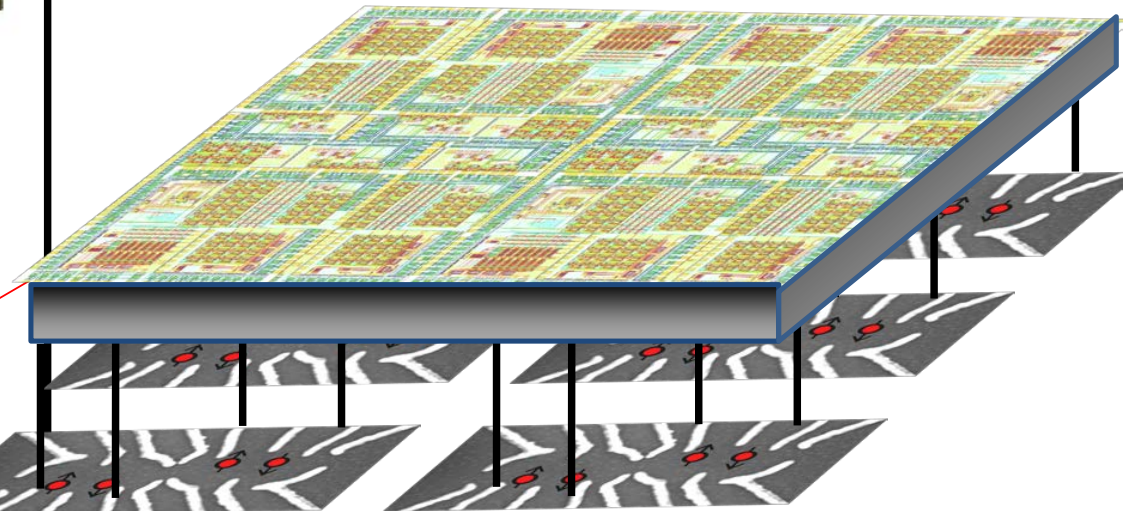
Vision of a Scalable QC

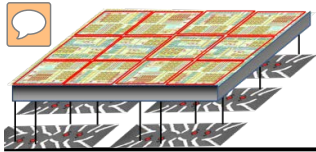


20 mK



Fully integrated semiconductor quantum processor with low-power integrated control logic

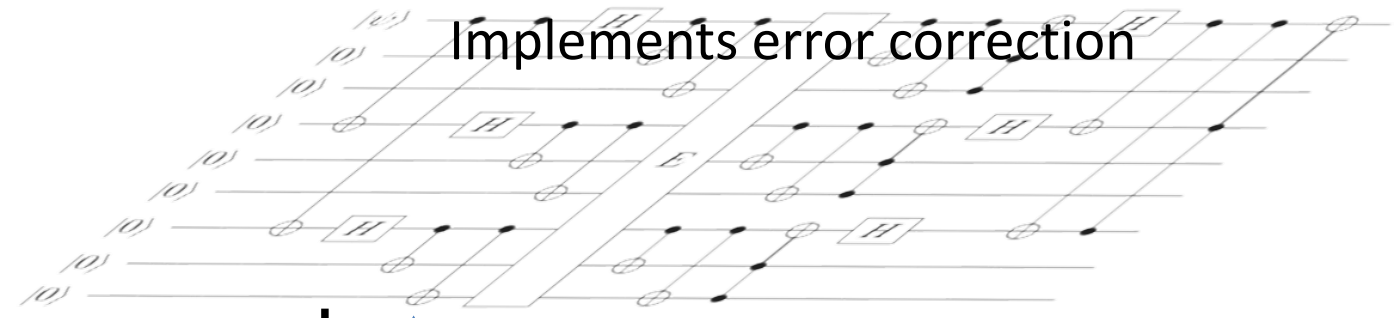




Low Level Architecture

High level control

Implements error correction

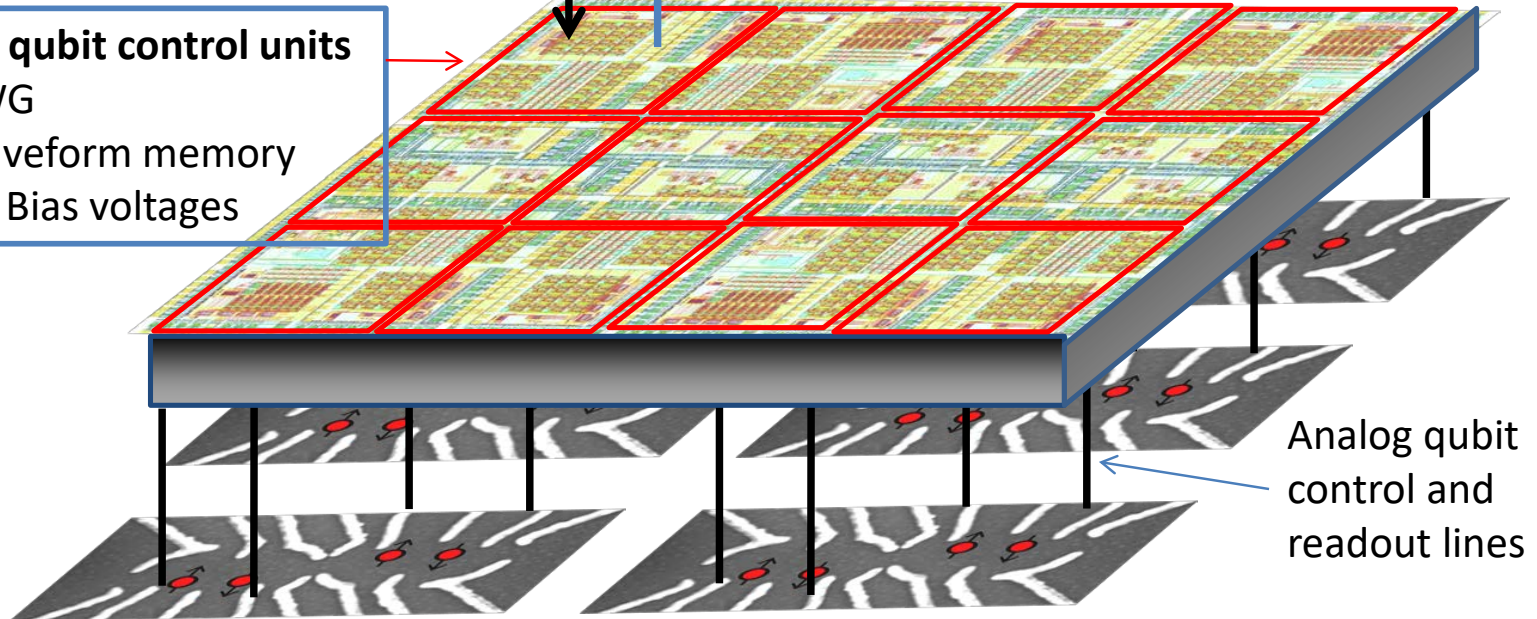


~4 bit digital command line

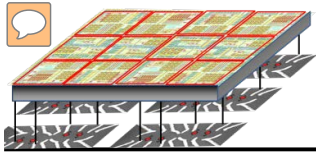
1 bit readout line

Single qubit control units

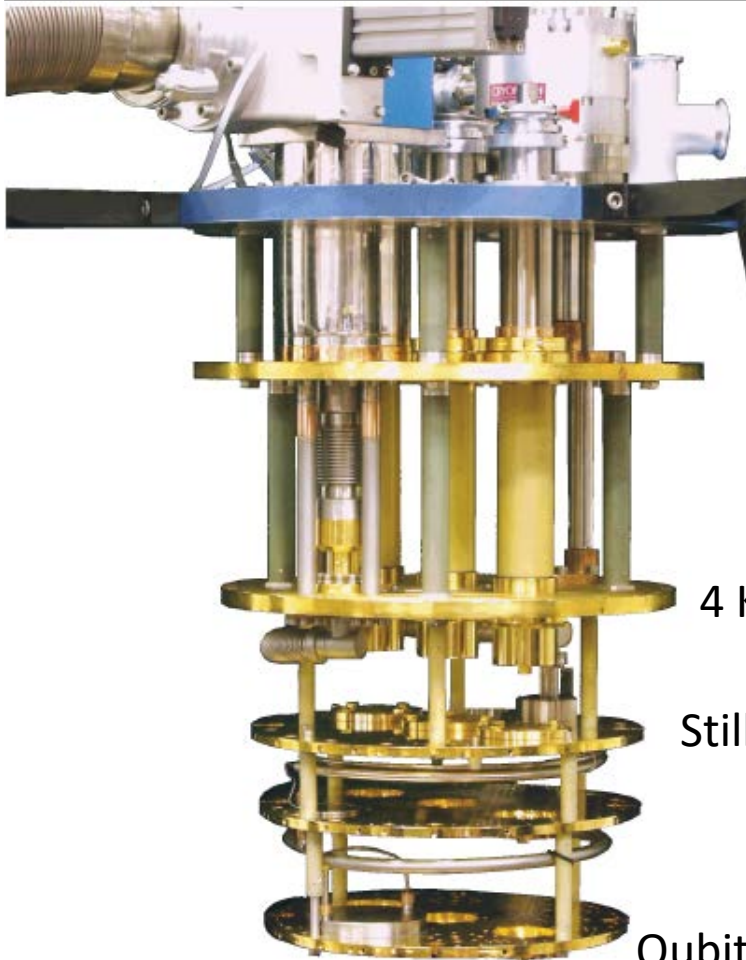
- AWG
- Waveform memory
- DC Bias voltages



Analog qubit control and readout lines



(Cooling) Power Budget



Premise: qubits operated at < 1 K

High cooling power, but hardly better than room temperature

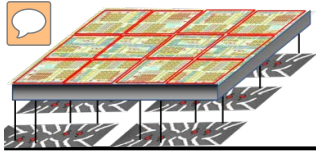
4 K, 5 W

Still: 0.7 K, 100 mW

Likely most relevant for control electronics

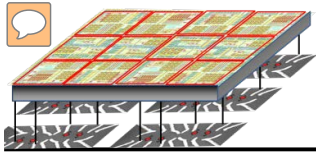
Qubit level: 100 mK, 1 mW.

=> Can dissipate at most a few nW per qubit

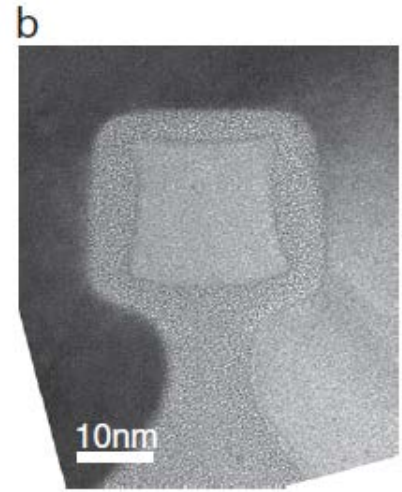
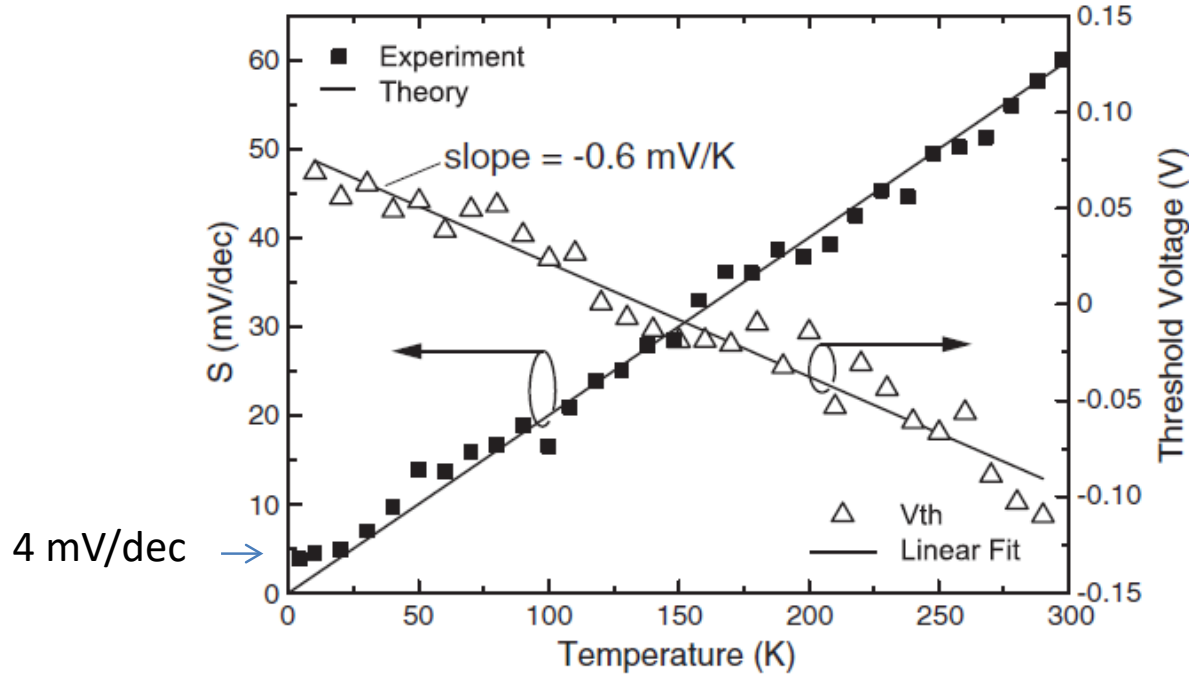


Useful Circumstances

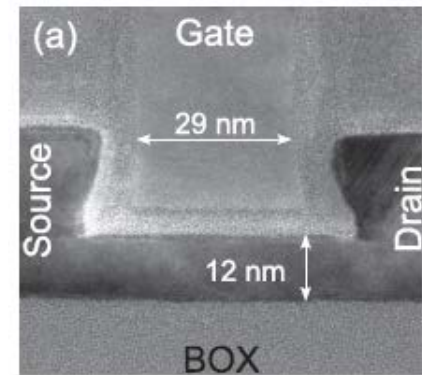
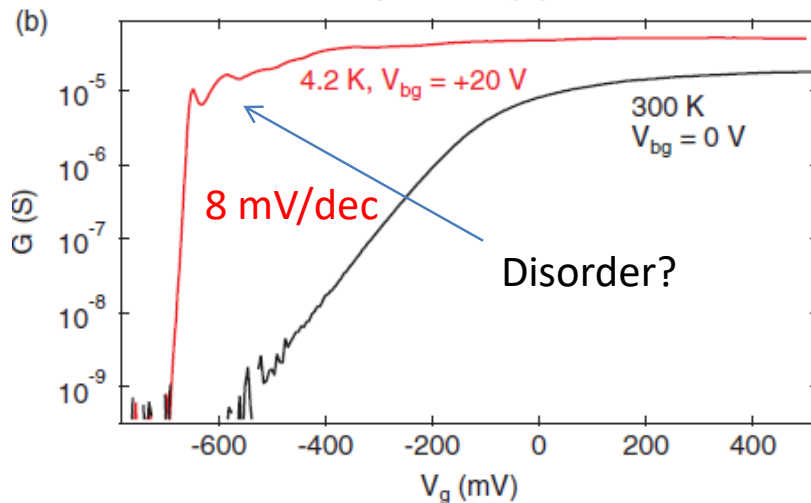
- Operation at ≤ 1 K
 - => $S = 0.2$ mV/decade (Thermal limit. Disorder ?)
 - => High mobility
 - Use $V_{dd} \approx 10$ mV (set by required output amplitude and speed)
- => Could operate at 10^{-10} W per transistor (at $f = 1$ GHz, $C = 1$ fF)
- Low leakage
- Purely capacitive loads (\sim fF scale) a few microns away
 - => No power-hungry signal transmission
- Superconducting wires
 - => Low dissipation, good thermal barriers.



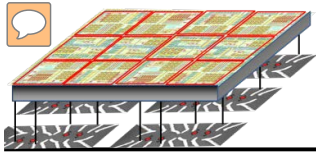
Steep Slope Transistors



S. Habicht et al., Thin Solid Films **520**, 3332 (2012)



B. Roche et al. App. Phys. Lett **100**, 032107 (2012)



Steep Slope Transistors



Demonstrated CMOS circuit operation:

$V_{dd} = 27 \text{ mV}$ at 77 K (but slow)

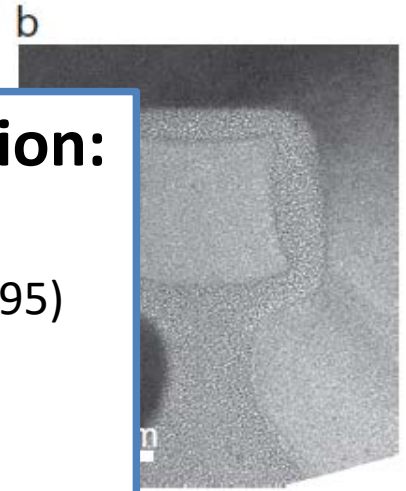
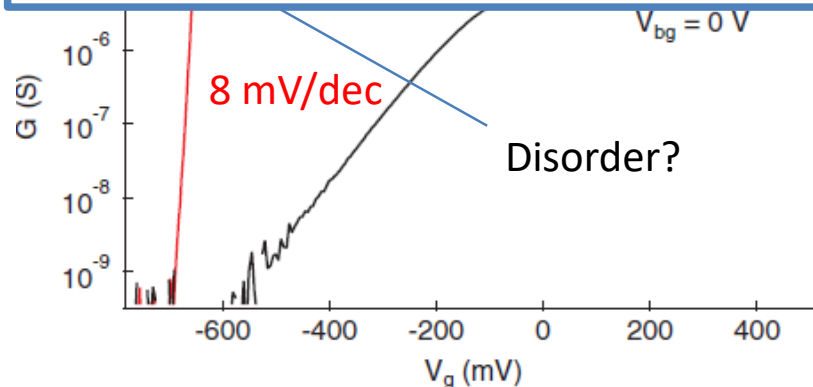
(J. Burr, Cryogenic Ultra Low Power CMOS, IEEE 1995)

Possible issues

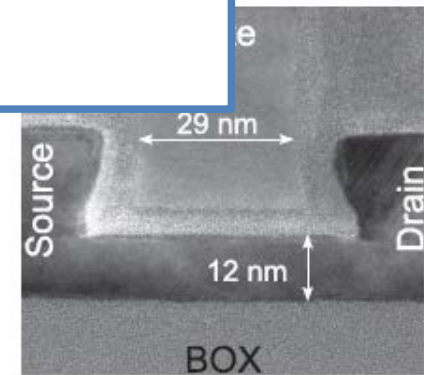
- Variability?
- Disorder limitation?
- Tuning of threshold voltage

S (mV/dec)

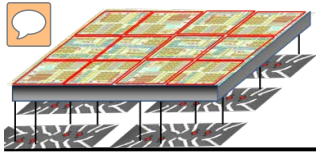
4 mV/dec



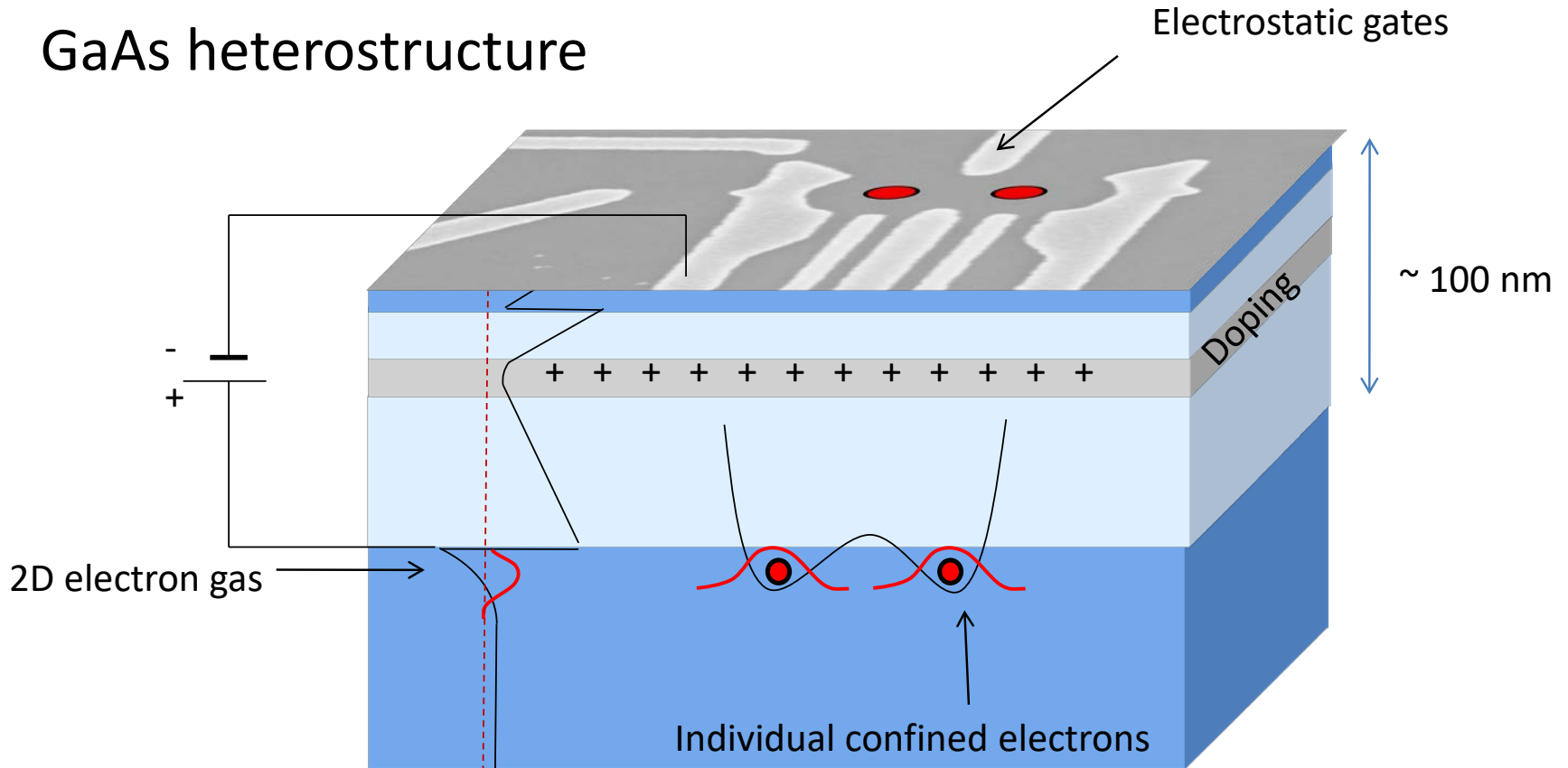
et al., Thin Solid
332 (2012)



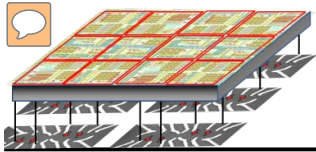
B. Roche et al. App. Phys. Lett
100, 032107 (2012)



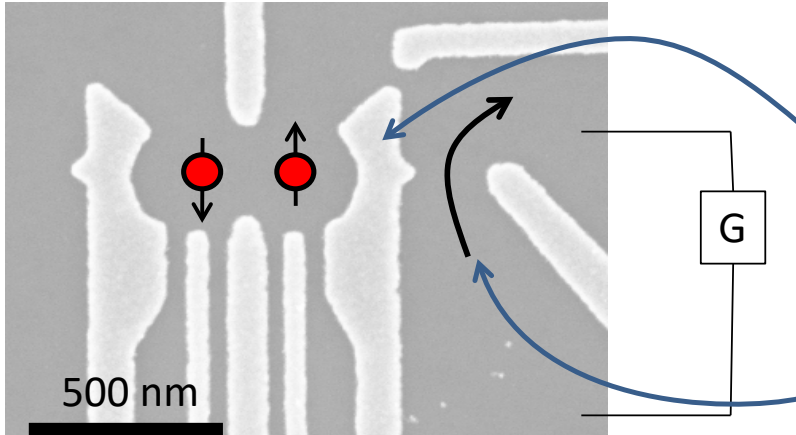
Gate-defined Quantum Dots



Scalable top down fabrication with standard lithography



Control of Two-electron Spin Qubits

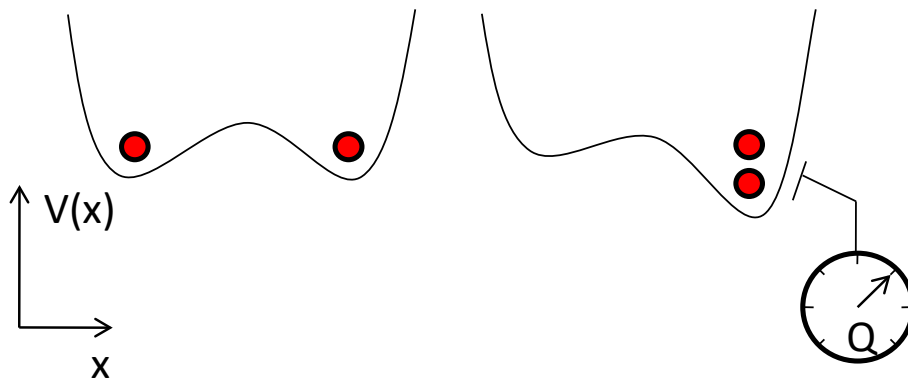


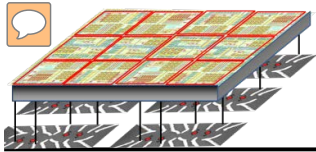
Resources needed

1 V level DC voltages to define and tune qubit

For readout: charge sensing
= 100 k Ω conductance measurement at
100 μ V / 1 nA bias

ns scale, mV level gate pulses for control



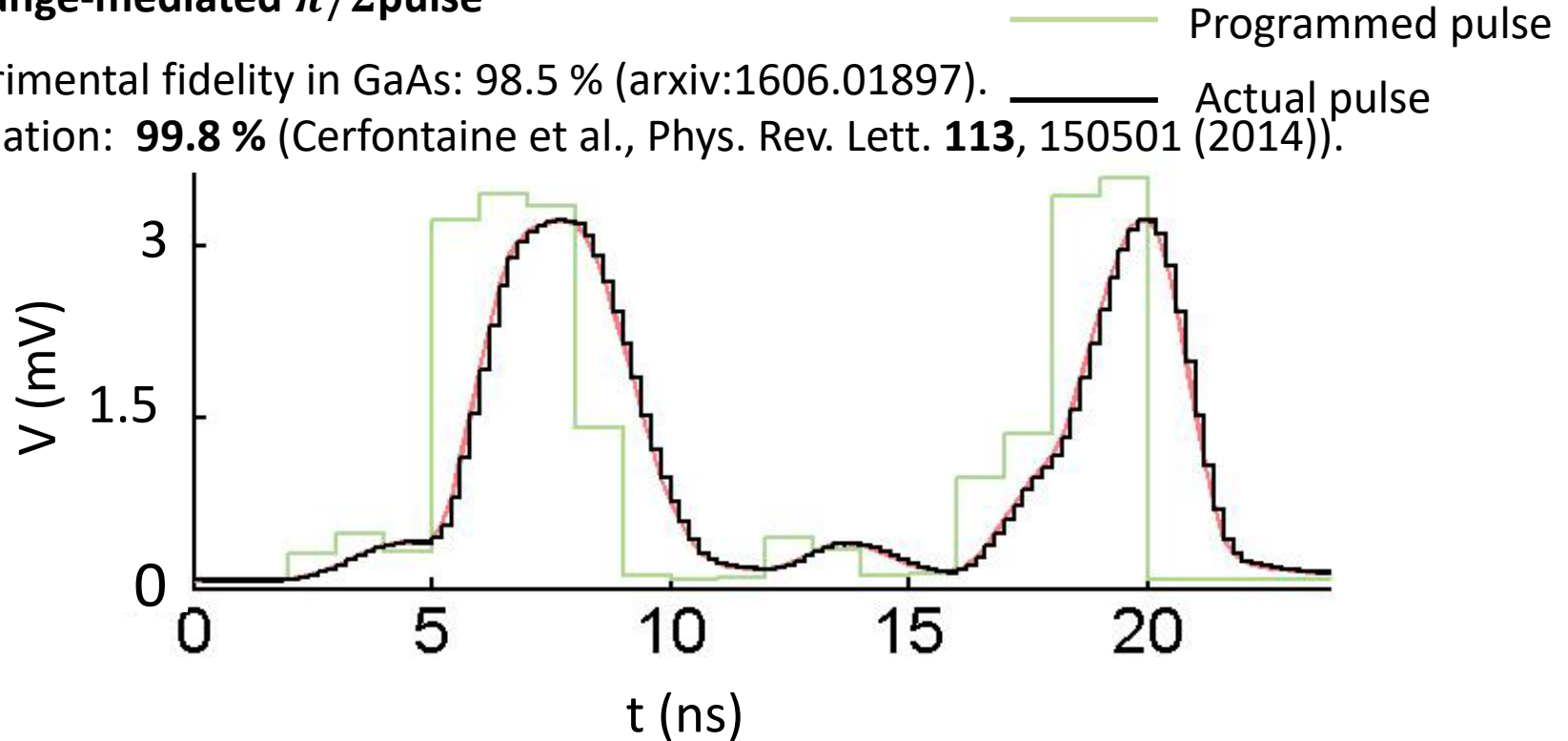


Anatomy of a Control Pulse

Exchange-mediated $\pi/2$ pulse

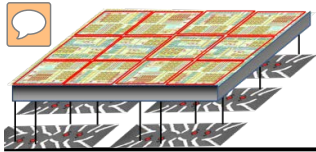
Experimental fidelity in GaAs: 98.5 % (arxiv:1606.01897).

Simulation: **99.8 %** (Cerfontaine et al., Phys. Rev. Lett. **113**, 150501 (2014)).



Hardware requirements:

- 1 GS/s (could be reduced to ~ 300 MS/s)
- 5 mV output
- ~ 8 bit resolution
- ~ 16 samples per gate

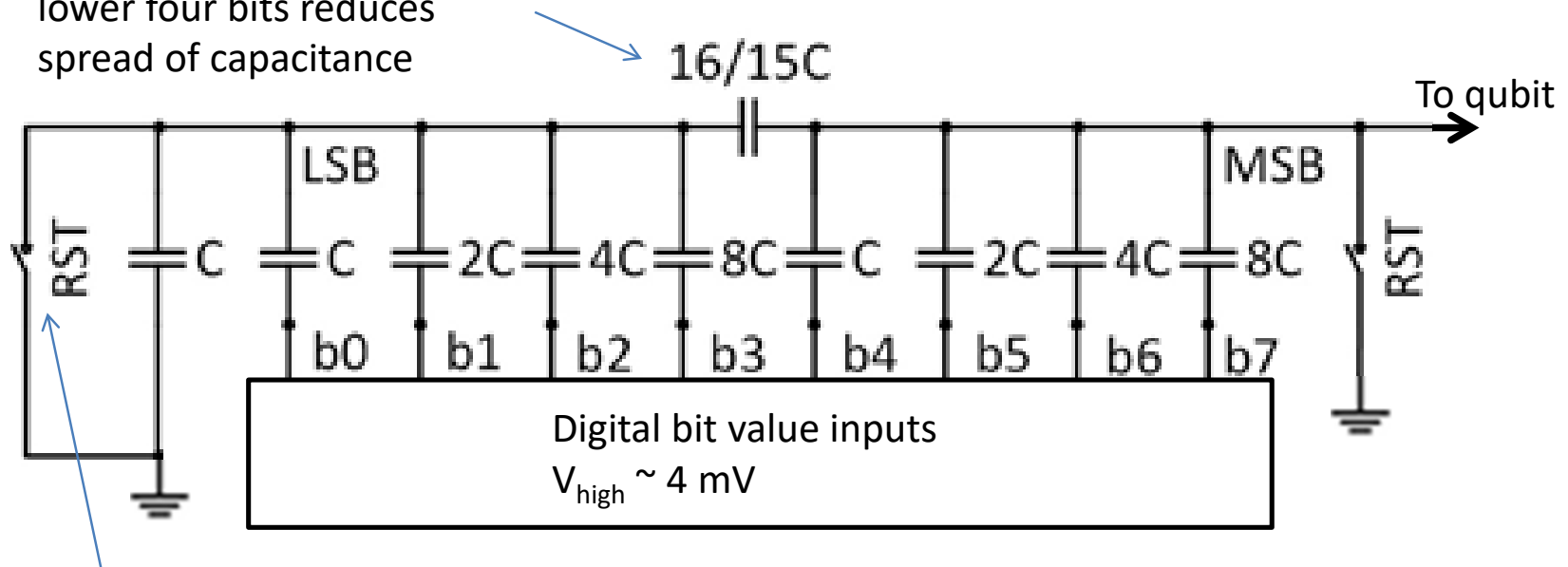


Low Power DAC Concept

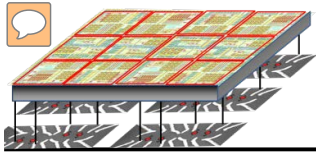
Capacitive voltage division

- No quiescent current
- No need for large integrated resistors
- Less sensitive to channel resistances than resistive division

Decoupling capacitor for lower four bits reduces spread of capacitance



Reset switches to compensate for leakage



AC Control System

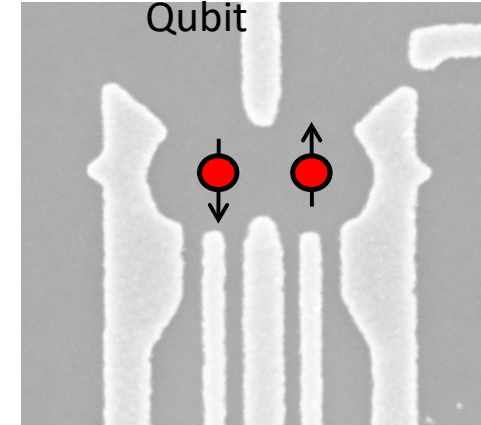
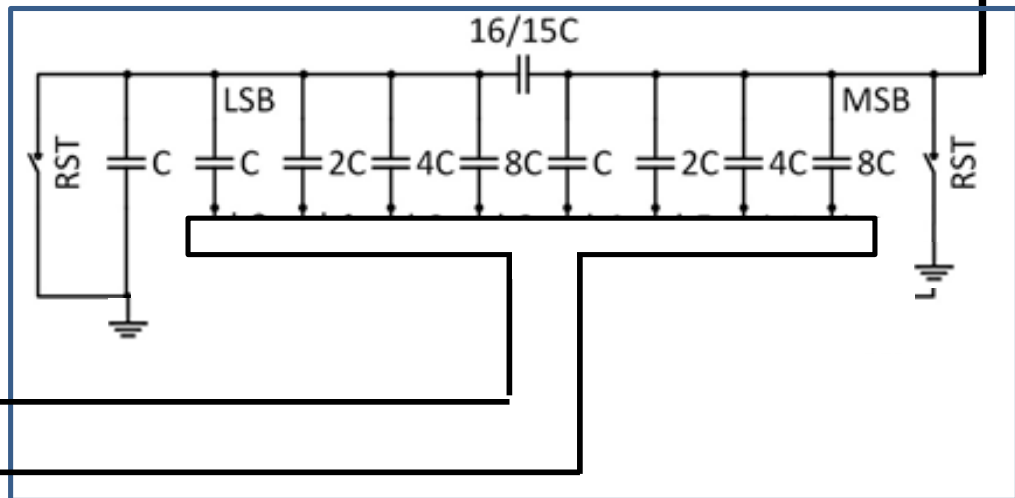
High level control

Instruction bus

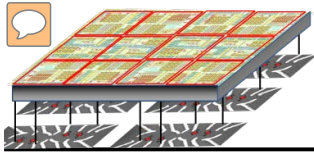
Memory

8 bit
16 samples per instruction
16 instructions per qubit
2 kbit per channel

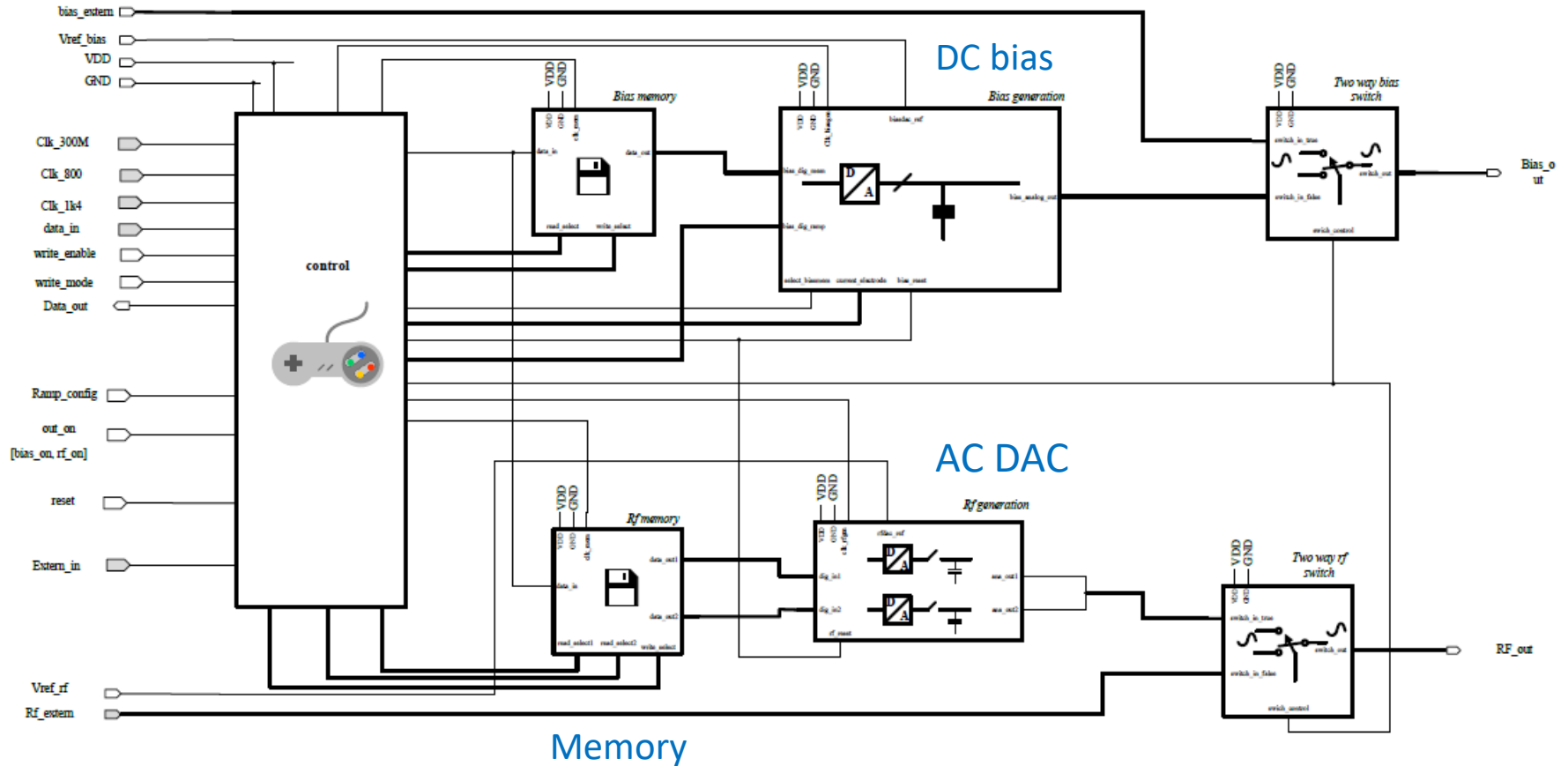
DAC (~ 300 MS/s)

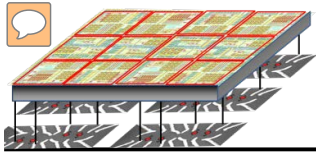


All in ultra-low power cryogenic CMOS



System Level Design Study





Noise and Size

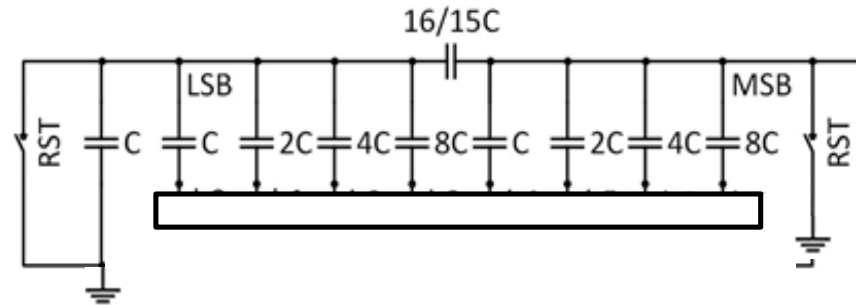
Thermal noise

Output capacitance

$$= 16 C \geq \frac{k_B T}{\langle \delta V^2 \rangle} = 0.5 \text{ fF}$$

for 0.2 nV/Hz output noise and $T = 0.2 \text{ K}$

Corresponds to $500 \mu\text{m}^2$ with $2 \text{ fF}/\mu\text{m}^2$ technology for DAC capacitors.



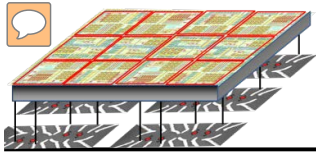
Transistor count

37.000 in control unit

36.000 for 2 kBits of memory

$14.000 \mu\text{m}^2 = 120 \times 120 \mu\text{m}$ at $0.25 \mu\text{m}^2$ per transistor.

=> Unit nearly small enough



Power and Speed

Power dissipation (DAC only)

$$8 C f_{\text{samp}} V_{\text{dd}}^2 = 2 \text{ nW}$$

$$\text{at } f_{\text{samp}} = 300 \text{ MS/s}, V_{\text{dd}} = 4 \text{ mV}$$

Switching speed

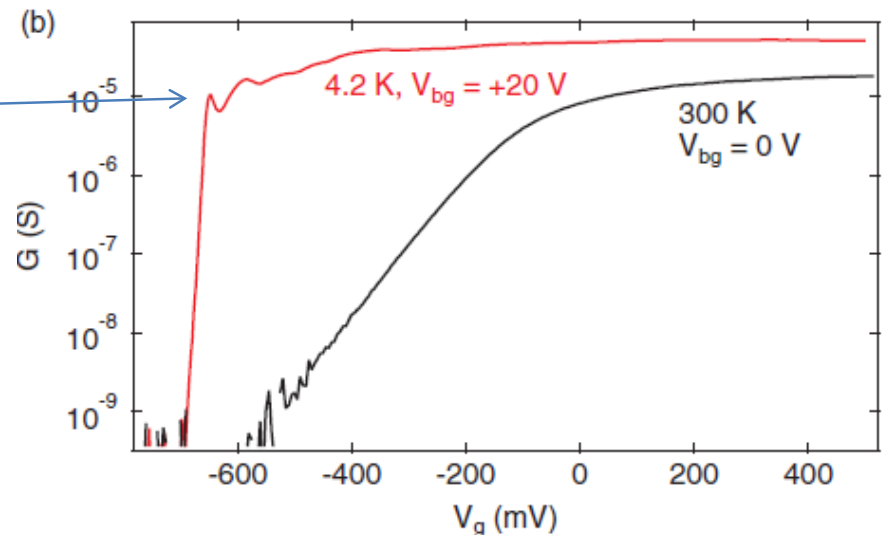
$$R_{\text{channel}} = 100 \text{ k}\Omega$$

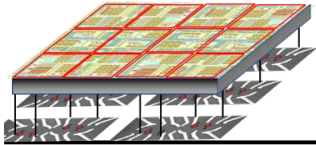
$$C_{\text{max}} = 4 C = 0.13 \text{ pF}$$

$$\Rightarrow \tau_{RC} = 13 \text{ ns}$$

=> Needs factor 10 improvement
compared to this unoptimized device

B. Roche et al. App. Phys. Lett
100, 032107 (2012)





Conclusion

- Integrated qubit control poses challenging but not impossible requirements on classical control circuits
- ~ 1 nW per qubit seems possible at low T seems possible, but requires a lot of rethinking, e.g.:
 - New transistors or different optimization targets
 - Specialized circuit designs

Outlook

- Similar concept also suitable for DC bias
- Could potentially be extended to microwave Rabi control with ultra low power modulators
=> Applicable to other qubit types